

BCM62B

PNP/PNP matched double transistor

Rev. 02 — 28 August 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP matched double transistor in a SOT143B small Surface-Mounted Device (SMD) plastic package. Matched version of BCV62.

NPN/NPN equivalent: BCM61B

1.2 Features

Current gain matching

1.3 Applications

- Current mirror
- Differential amplifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor TR1					
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_C = -2 \text{ mA}$	200	290	450	
Per transis	stor					
I _C	collector current		-	-	-100	mA
Per device	•					
I _{C1} /I _{E2}	current matching	$V_{CE1} = -5 \text{ V};$ $I_{E2} = 0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	<u>11</u> 1	1.1	1.2	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





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2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Symbol
1	collector TR2, base TR1 and TR2		
2	collector TR1	4 3	4 3
3	emitter TR1		TR2
4	emitter TR2	1 2	
			1 2
			006aaa843

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BCM62B	-	plastic surface-mounted package; 4 leads	SOT143B

4. Marking

Table 4. Marking codes

Type number	Marking code[1]
BCM62B	*AD

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor TR1				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-45	V
Per transis	stor				
V _{EBS}	emitter-base voltage	$V_{CB} = 0 V$	-	-5	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	220	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	390	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	568	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	321	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor TR1					
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	–15	nA
		$V_{CB} = -30 \text{ V};$ $I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	- 5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V};$ $I_{C} = 0 \text{ A}$	-	-	-100	nA
h _{FE}	h _{FE} DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \mu\text{A}$	-	250	-	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	100	-	-	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	200	290	450	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	-50	-200	mV
		$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$	-	-200	-400	mV
V _{BEsat} base-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	<u>[1]</u> -	-760	-	mV	
	$I_C = -100 \text{ mA};$ $I_B = -5 \text{ mA}$	<u>[1]</u> _	-920	-	mV	
V_{BE}	base-emitter voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -2 \text{ mA}$	<u>[2]</u> –600	-650	-700	mV
		$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA}$	[2] _	-	-760	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.2	pF
C _e	emitter capacitance	$V_{EB} = -0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	10	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	100	175	-	MHz
NF noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ 15.7 kHz	-	1.6	-	dB	
		$V_{CE} = -5 \text{ V};$ $I_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 1 \text{ kHz};$ $B = 200 \text{ Hz}$	-	3.1	-	dB

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Table 7. Characteristics ...continued $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

amb =c	- :			_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor TR2					
V _{EBS} emitter-base voltage	emitter-base voltage	$V_{CB} = 0 \text{ V};$ $I_E = 250 \text{ mA}$	-	-	1.5	V
	$V_{CB} = 0 \text{ V};$ $I_E = 10 \mu\text{A}$	400	-	-	mV	
Per device	9					
I _{C1} /I _{E2} current matching	$V_{CE1} = -5 \text{ V};$ $I_{E2} = 0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>3</u>] 1	1.1	1.2		
	$V_{CE1} = -5 \text{ V};$ $I_{E2} = 0.5 \text{ mA};$ $T_{amb} \le 150 \text{ °C}$	³ 1.02	-	1.22		
		$V_{CE1} = -3 \text{ V};$ $I_{E2} = 0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>3</u>] 0.95	1.05	1.15	
		$V_{CE1} = -1 \text{ V};$ $I_{E2} = 0.5 \text{ mA};$ $T_{amb} \le 25 \text{ °C}$	[<u>3</u>] 0.9	1	1.1	

^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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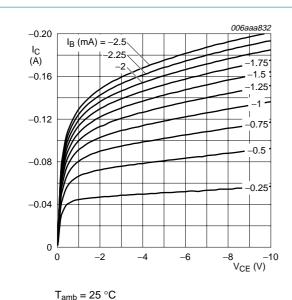
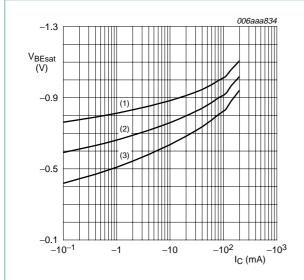


Fig 1. Collector current as a function of collector-emitter voltage; typical values



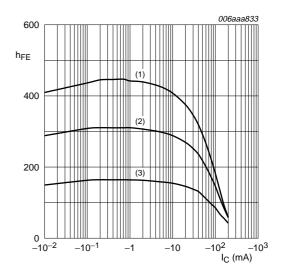
 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = -55 \,^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



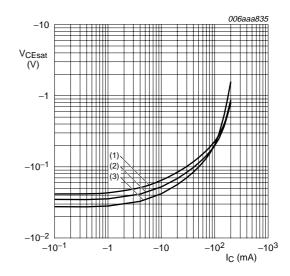
 $V_{CE} = -5 \text{ V}$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 2. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

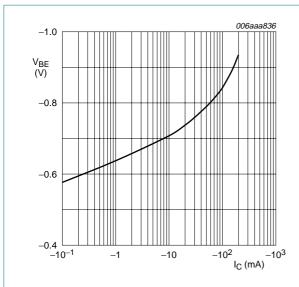
(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 4. Collector-emitter saturation voltage as a function of collector current; typical values

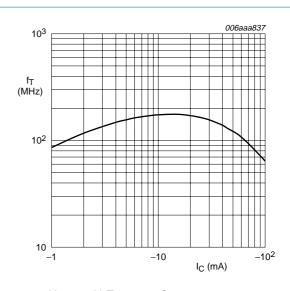
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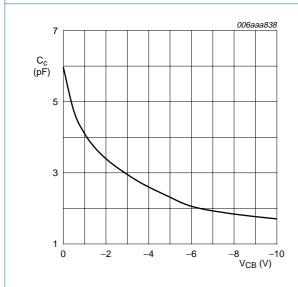
 $V_{CE} = -5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 5. Base-emitter voltage as a function of collector current; typical values



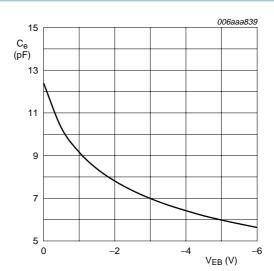
 $V_{CE} = -5$ V; $T_{amb} = 25\ ^{\circ}C$

Fig 6. Transition frequency as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

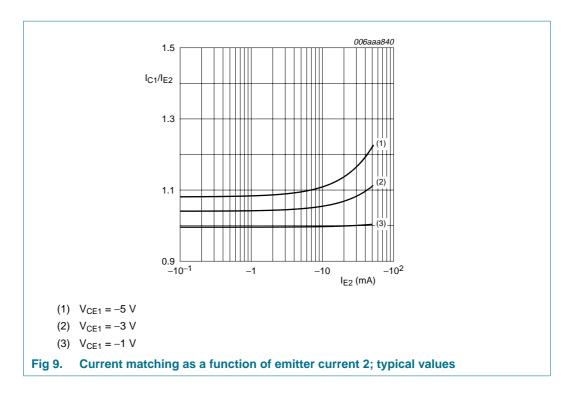
Fig 7. Collector capacitance as a function of collector-base voltage; typical values



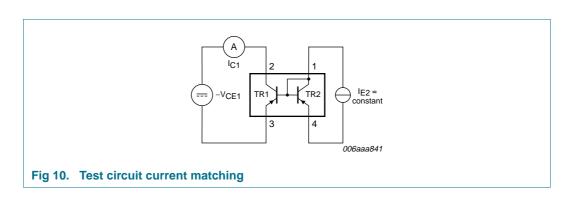
 $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$

Fig 8. Emitter capacitance as a function of emitter-base voltage; typical values

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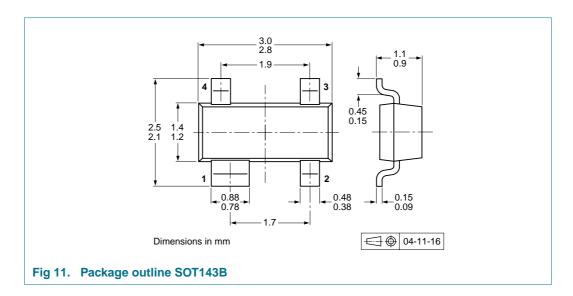


8. Test information



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9. Package outline



10. Packing information

Table 8. Packing methods

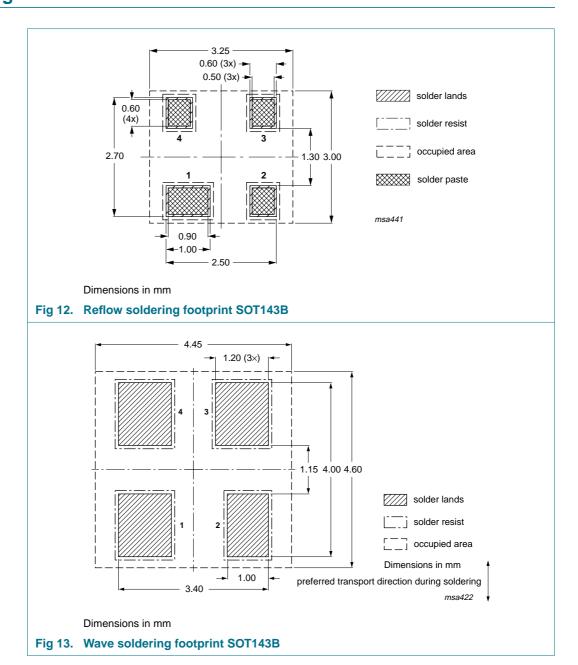
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qua	intity
			3000	10000
BCM62B	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BCM62B_2	20090828	Product data sheet	-	BCM62B_1
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors including new legal definitions and disclaimers. No changes were made to the technic content. 			
	• Figure 13 "\	Nave soldering footprint So	OT143B":updated	
BCM62B_1	20060919	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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